(An Autonomous Institution)

19EET202 / ANALOG ELECTRONI

II YEAR / III SEMESTER

UNIT-2: MULTI JUNCTION DEVICES

1

MOSFET

We'll Discuss

INE

Wh

2

Structure

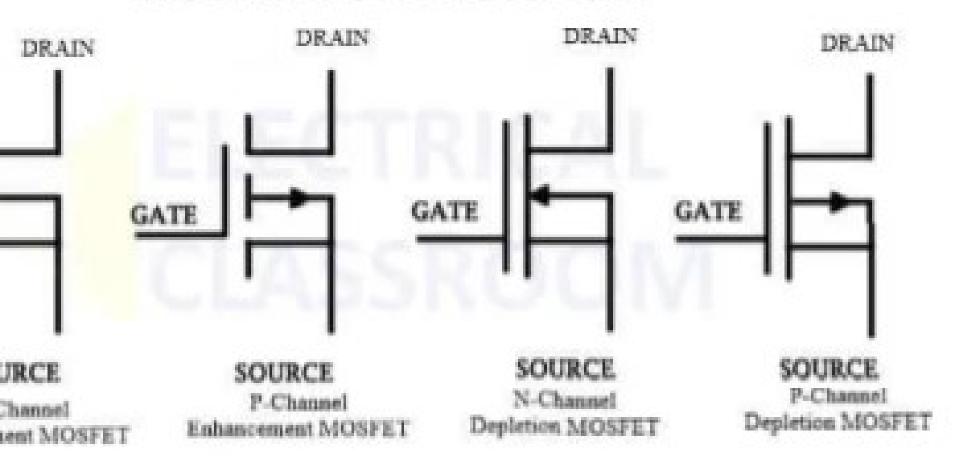
de Semiconductor Field Effect Transistors

voltage controlled devices, in which the current flowind drain is proportional to the provided input voltage.

Thas a smaller value of capacitance and its input imped re than that of FET due to small leakage current.

oplication widely in switching and amplification of elections of its ability to change conductivity with the apple

MOSFET SYMBOLS



n two modes-

ode: The transistor requires the Gate-Source voltage (VGS) to ne depletion-mode MOSFET is equivalent to a "Normally Close

t Mode: The transistor requires a Gate-Source voltage(VGS) to e enhancement mode MOSFET is equivalent to a "Normally C

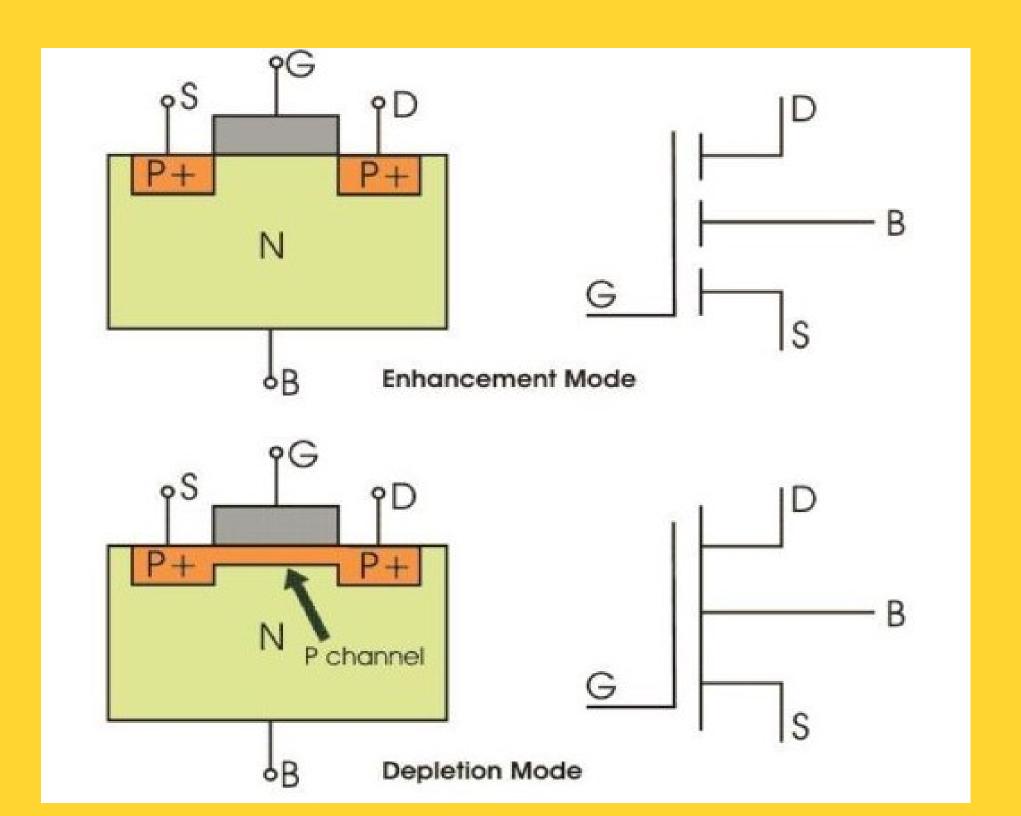
ct to the working principle, MOSFET is classified as follows:

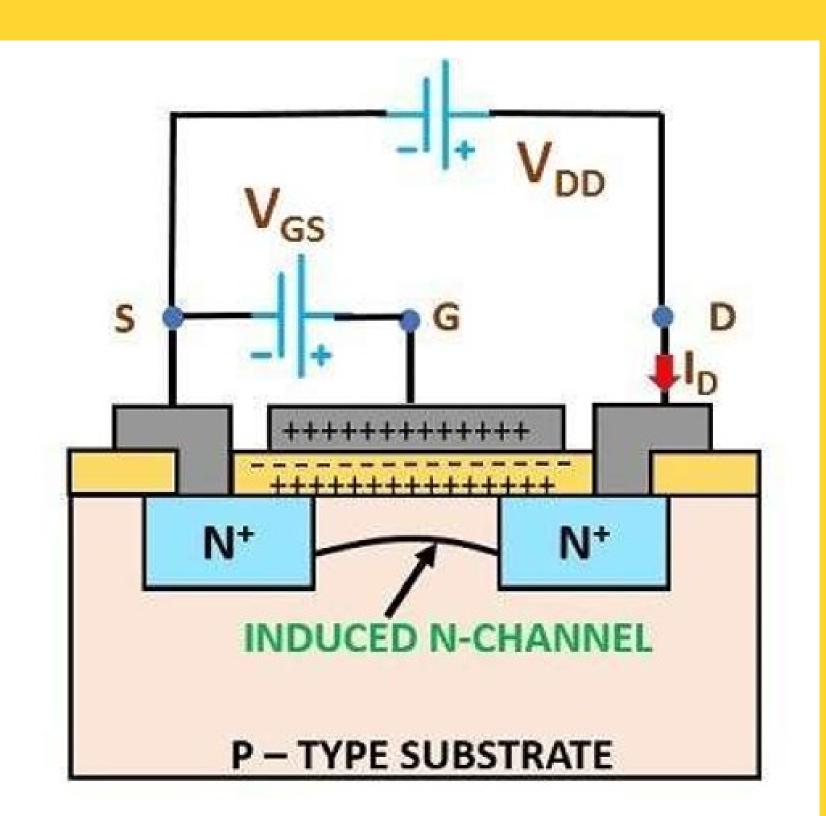
etion MOSFET

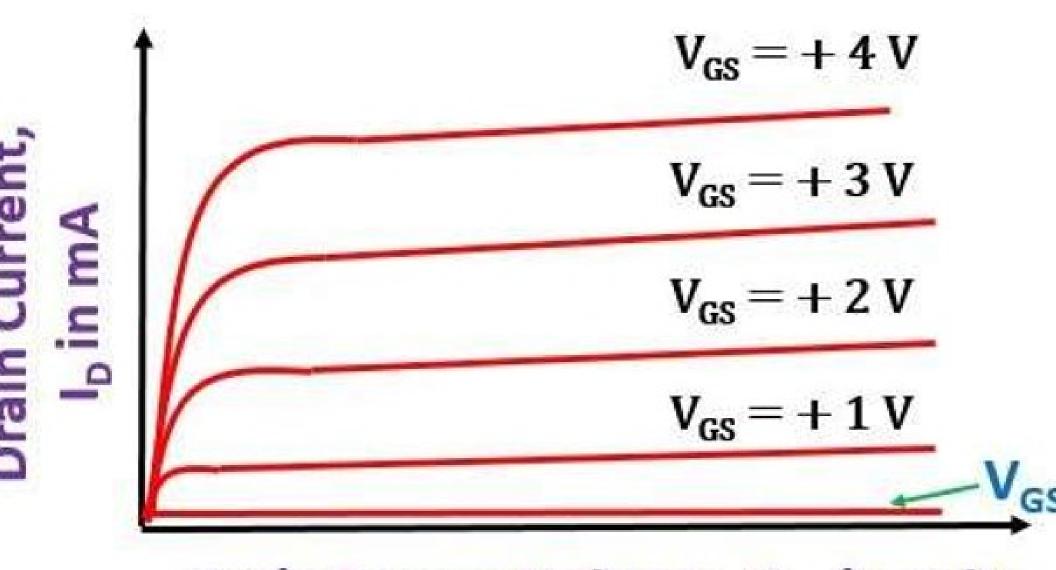
ncement MOSFET

etion MOSFET

ncement MOSFET



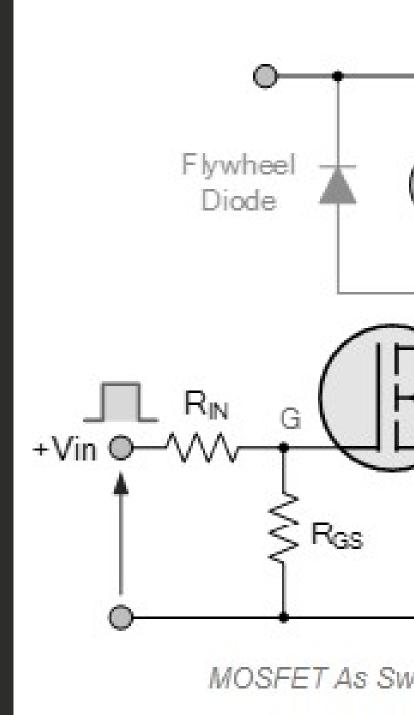




Drain Source Voltage, V_{DS} in volts

IS	ВЈТ	FET	MOSFE
уре	Current controlled	Voltage controlled	Voltage Cont
flow	Bipolar	Unipolar	Unipola
als	Not interchangeable	Interchangeable	Interchange
modes	No modes	Depletion mode only	Both Enhance and Depletion
edance	Low	High	Very hig
istance	Moderate	Moderate	Low
l speed	Low	Moderate	High
9	High	Low	Low
ability	Low	Better	High

DC Motors of Chopper Amplifiers Amplifying Signals T as a Switch



be used in the making of must work in

triode region can be

n the saturation region a te as an amplifier.

11

2. For MOSFET is to be then it must operate in a) Cut-off region b) Triode region c) Saturation region d) Both cut-off and trio used

Answer: d Explanation: In both reg

the task of a switch.

THANK